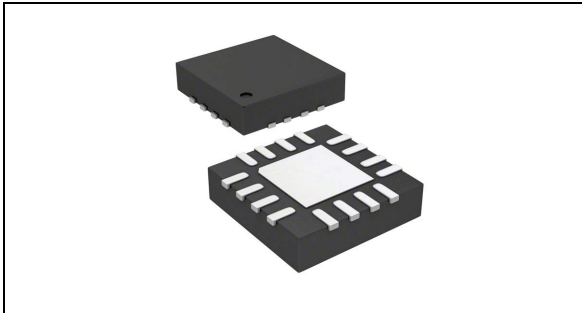


Low voltage brush DC motor driver

Datasheet - production data

**Features**

- Operating voltage from 1.8 to 10 V
- Maximum output current 2.6 A_{rms} with OUTAx paralld to OUTBx
- R_{DS(ON)} HS + LS = 0.2 Ω typ.
- Current control with programmable off-time
- Full protection set
 - Non-dissipative overcurrent protection
 - Short-circuit protection
 - Thermal shutdown
- Energy saving and long battery life with standby consumption less than 80 nA

Applications

Battery-powered DC motor applications such as:

- Toys
- Portable printers
- Robotics
- Point of sales (POS) devices
- Portable medical equipment
- Healthcare and wellness devices (shavers and toothbrushes)

Description

The STSPIN250 is a single brush DC motor driver integrating a low R_{ds(ON)} power stage in a small VFQFPN 3 x 3 mm package.

The full-bridge implements a PWM current controller with fixed OFF time.

The device is designed to operate in battery-powered scenarios and can be forced in a zero-consumption state allowing a significant increase in battery life.

The device offers a complete set of protection features including overcurrent, overtemperature and short-circuit protection.

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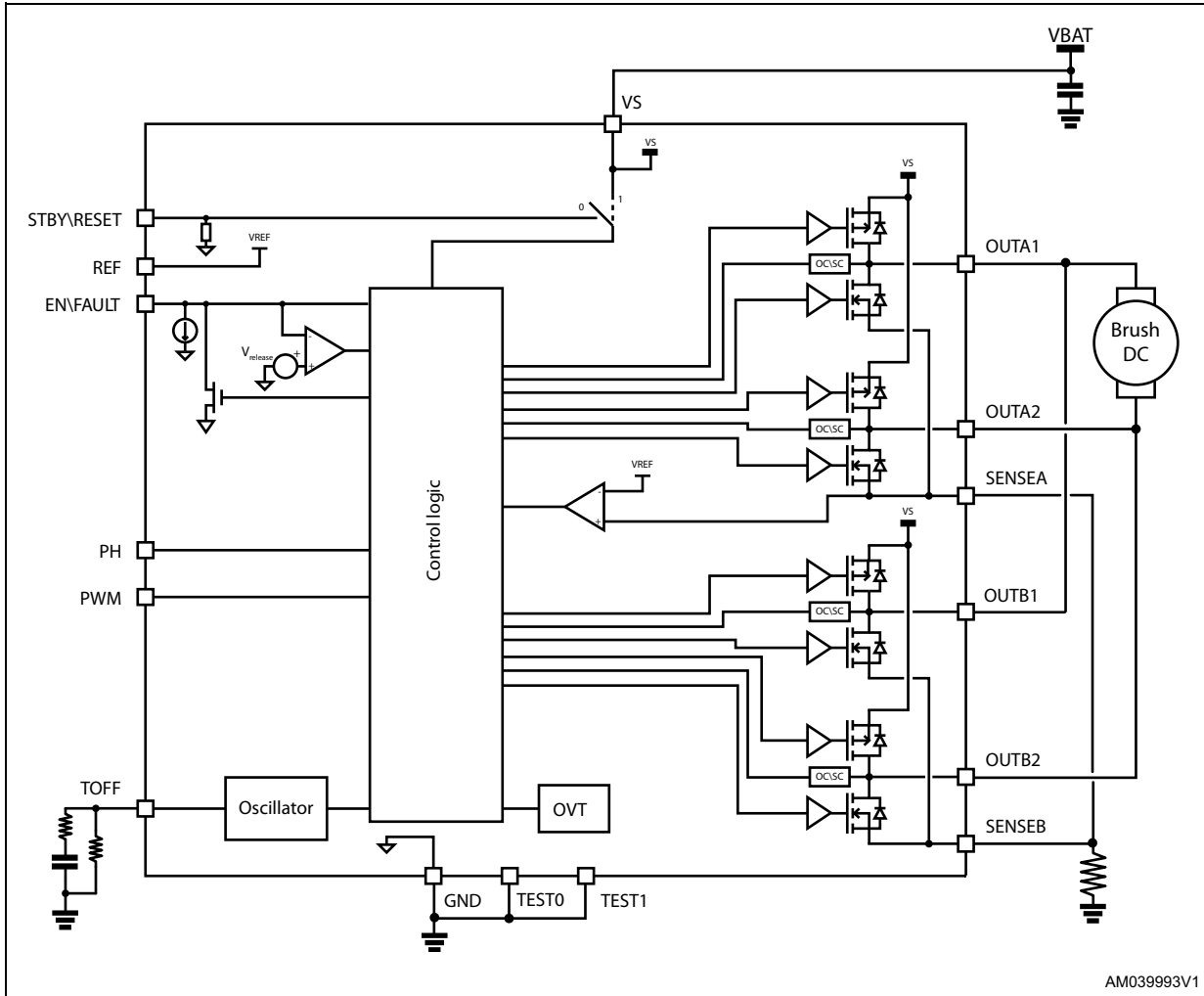
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1 Block diagram

Figure 1. Block diagram



2 Electrical data

2.1 Absolute maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Test condition	Value	Unit
V_S	Supply voltage	-	-0.3 to 11	V
V_{IN}	Logic input voltage	-	-0.3 to 5.5	V
$V_{OUT} - V_{SENSE}$	Output to sense voltage drop	-	up to 12	V
$V_S - V_{OUT}$	Supply to output voltage drop	-	up to 12	V
V_{SENSE}	Sense pins voltage	-	-1 to 1	V
V_{REF}	Reference voltage input	-	-0.3 to 1	V
$I_{OUT,RMS}$	Continuous power stage output current (OUTAx // OUTBx)	-	2.6	Arms
$T_{j,OP}$	Operative junction temperature	-	-40 to 150	°C
$T_{j,STG}$	Storage junction temperature	-	-55 to 150	°C

2.2 Recommended operating conditions

Table 2. Recommended operating conditions

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
V_S	Supply voltage	-	1.8	-	10	V
V_{IN}	Logic input voltage	-	0	-	5	V
V_{REF}	Reference voltage input	-	0.1	-	0.5	V
t_{INw}	Logic input positive/negative pulse width	-	300	-	-	ns

2.3 Thermal data

Table 3. Thermal data

Symbol	Parameter	Conditions	Value	Unit
R_{thJA}	Junction to ambient thermal resistance	Natural convection, according to JESD51-2A ⁽¹⁾	57.1	°C/W
$R_{thJCTop}$	Junction to case thermal resistance (top side)	Simulation with cold plate on package top	67.3	°C/W
$R_{thJCbot}$	Junction to case thermal resistance (bottom side)	Simulation with cold plate on exposed pad	9.1	°C/W
R_{thJB}	Junction to board thermal resistance	According to JESD51-8 ⁽¹⁾	23.3	°C/W
Ψ_{JT}	Junction to top characterization	According to JESD51-2A ⁽¹⁾	3.3	°C/W
Ψ_{JB}	Junction to board characterization	According to JESD51-2A ⁽¹⁾	22.6	°C/W

1. Simulated on a 21.2 x 21.2 mm board, 2s2p 1 Oz copper and four 300 μ m via below exposed pad.

2.4 ESD protections

Table 4. ESD protection ratings

Symbol	Parameter	Test condition	Class	Value	Unit
HBM	Human body model	Conforming to ANSI/ESDA/JEDEC JS-001-2014	H2	2	kV
CDM	Charge device model	Conforming to ANSI/ESDA/JEDEC JS-001-2014	C2a	500	V

3 Electrical characteristics

Testing conditions: $V_S = 5\text{ V}$, $T_j = 25\text{ °C}$, unless otherwise specified.

Table 5. Electrical characteristics

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
Supply						
$V_{Sth(ON)}$	V_S turn-on voltage	V_S rising from 0 V	1.45	1.65	1.79	V
$V_{Sth(OFF)}$	V_S turn-off voltage	V_S falling from 5 V	1.3	1.45	1.65	V
$V_{Sth(HYS)}$	V_S hysteresis voltage	-	-	180		mV
I_S	V_S supply current	No commutations EN = 0 $R_{OFF} = 160\text{ k}\Omega$	-	960	1300	μA
		No commutations EN = 1 $R_{OFF} = 160\text{ k}\Omega$	-	1500	1950	μA
$I_{S,STBY}$	V_S standby current	STBY = 0 V	-	10	80	nA
V_{STBYL}	Standby low logic level input voltage	-	-	-	0.9	V
V_{STBYH}	Standby logic level input voltage	-	1.48	-	-	V
Power stage						
$R_{DS(ON)HS+LS}$	Total on resistance HS + LS ⁽¹⁾ (OUTAx // OUTBx)	$V_S = 10\text{ V}$ $I_{OUT} = 1.3\text{ A}$	-	0.2	0.33	Ω
		$V_S = 10\text{ V}$ $I_{OUT} = 1.3\text{ A}$ $T_j = 125\text{ °C}^{(2)}$	-	0.27	0.44	
		$V_S = 3\text{ V}$, $I_{OUT} = 0.4\text{ A}$	-	0.27	0.4	
I_{DSS}	Leakage current	OUTx = V_S	-	-	1	μA
		OUTx = GND	-1	-	-	
V_{DF}	Freewheeling diode forward voltage	$I_D = 1.3\text{ A}$	-	0.9	-	V
t_{rise}	Rise time	$V_S = 10\text{ V}$; unloaded outputs	-	10	-	ns
t_{fall}	Fall time	$V_S = 10\text{ V}$; unloaded outputs	-	10	-	ns
t_{DT}	Dead time	-	-	50	-	ns
PWM current controller						
$V_{SNS,OFFSET}$	Sensing offset	$V_{REF} = 0.5\text{ V}$ Internal reference 20% V_{REF}	-15	-	+15	mV
t_{OFF}	Total OFF time	$R_{OFF} = 10\text{ k}\Omega$	-	9	-	μs
		$R_{OFF} = 160\text{ k}\Omega$	-	125	-	μs



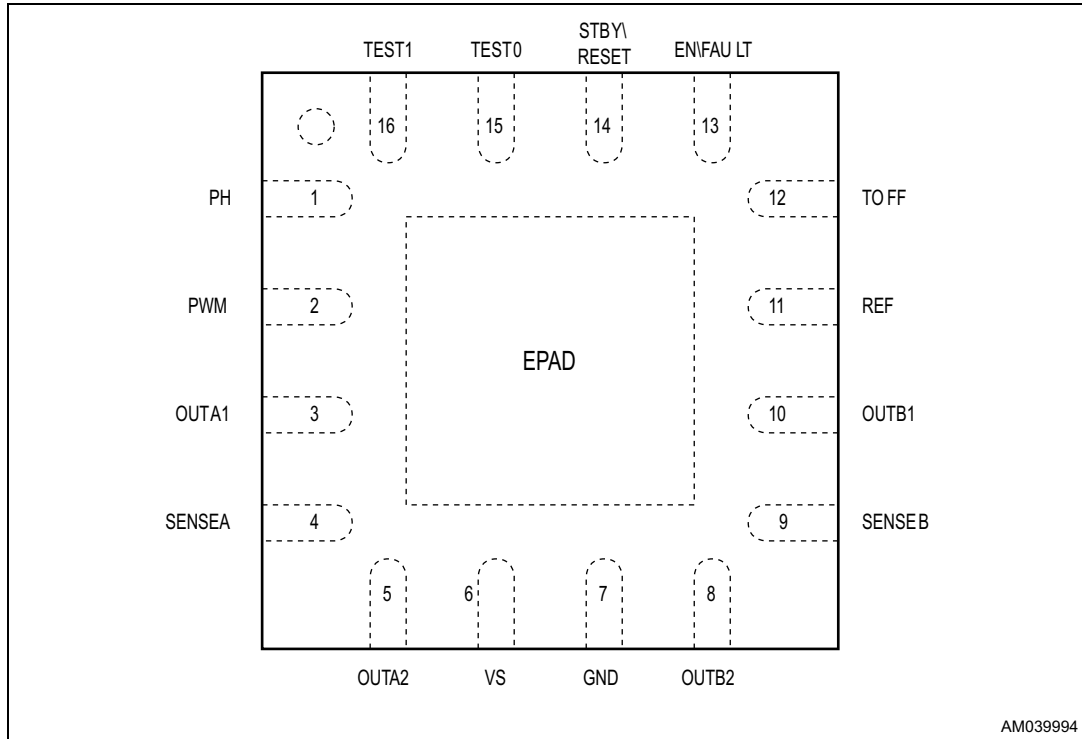
Table 5. Electrical characteristics (continued)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
Δf_{OSC}	Oscillator precision	$f_{OSC}/f_{OSC,ID}$	-20%	-	+20%	-
$t_{OFF,jitter}$	Total OFF time jittering	$R_{OFF} = 10\text{ k}\Omega$	-	-	2%	-
Logic IOs						
V_{IH}	High logic level input voltage	-	1.6	-	-	V
V_{IL}	Low logic level input voltage	-	-	-	0.6	V
$V_{RELEASE}$	FAULT open drain release voltage	-	-	-	0.4	V
V_{OL}	Low logic level output voltage	$I_{OL} = 4\text{ mA}$	-	-	0.4	V
R_{STBY}	STBY pull-down resistance	-	-	36	-	$\text{k}\Omega$
I_{PDEN}	EN pull-down current	-	-	10.5	-	μA
t_{END}	EN input propagation delay	From EN falling edge to OUT high impedance	-	55	-	ns
$t_{PWM,d(ON)}$	PWM turn-on propagation delay	See Figure 4 on page 14	-	125	-	ns
$t_{PWM,d(OFF)}$	PWM turn-off propagation delay	See Figure 4	-	140	-	ns
$t_{PH,d}$	PH propagation delay	See Figure 4	-	125	-	ns
Protections						
T_{JSD}	Thermal shutdown threshold	-	-	160	-	$^{\circ}\text{C}$
$T_{JSD,Hyst}$	Thermal shutdown hysteresis	-	-	40	-	$^{\circ}\text{C}$
I_{OC}	Overcurrent threshold	Single OUT	-	2	-	A
		OUTAx // OUTBx	-	4	-	

1. Production test made on single outputs.
2. Based on characterization data on a limited number of samples, not tested during production.

4 Pin description

Figure 2. Pin connection (top view)



Note: The exposed pad, TEST0 and TEST1 pins must be connected to ground.
 OUTA1 and OUTB1 must be connected together.
 OUTA2 and OUTB2 must be connected together.
 SENSEA and SENSEB must be connected together.

Table 6. Pin description

No.	Name	Type	Function
1	PH	Logic input	Phase input
2	PWM	Logic input	PWM input
3	OUTA1	Power output	Power bridge output side A1, must be connected to OUTB1.
4	SENSEA	Power output	Sense output A, must be connected to SENSEB.
5	OUTA2	Power output	Power bridge output side A2, must be connected to OUTB2.
6	VS	Supply	Device supply voltage.
7, EPAD	GND	Ground	Device ground.
8	OUTB2	Power output	Power bridge output side B2, must be connected to OUTA2.
9	SENSEB	Power output	Sense output B, must be connected to SENSEA.

Table 6. Pin description (continued)

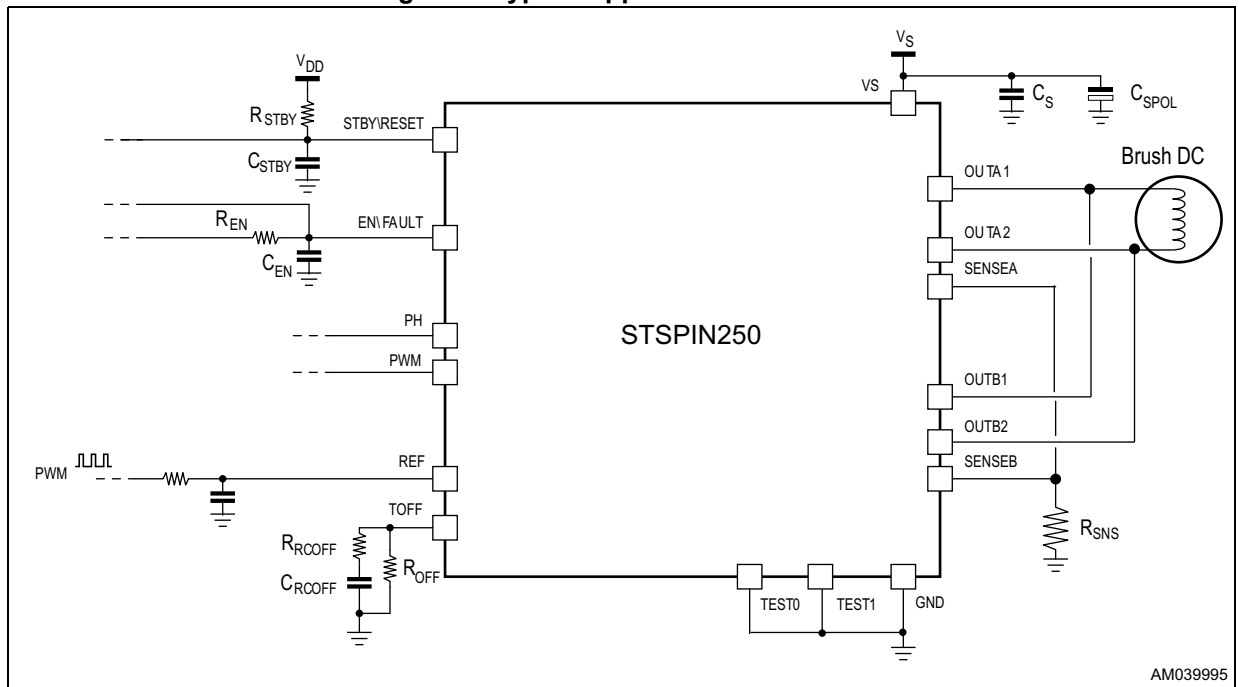
No.	Name	Type	Function
10	OUTB1	Power output	Power bridge output side B1, must be connected to OUTA1.
11	REF	Analog input	Reference voltage for the current limiter circuitry.
12	TOFF	Analog input	Internal oscillator frequency adjustment.
13	ENFAULT	Logic input/ open drain output	Logic input 5 V compliant whit and open drain output. This is the power stage enable (when low the power stage is turned off) and it is forced low through the integrated open-drain MOSFET when a failure occurs.
14	STBY\RESET	Logic input	Logic input 5 V compliant. When forced low the device is forced into the low consumption mode.
15	TEST0	-	Reserved pin. This pin must be connected to ground.
16	TEST1	-	Reserved pin. This pin must be connected to ground.

5 Typical applications

Table 7. Typical application values

Name	Value
C_S	2.2 μF / 16 V
C_{SPOL}	22 μF / 16 V
R_{SNS}	330 m Ω / 1 W
C_{EN}	10 nF / 6.3 V
R_{EN}	18 k Ω
C_{STBY}	1 nF / 6.3 V
R_{STBY}	18 k Ω
C_{RCOFF}	22 nF
R_{RCOFF}	1 k Ω
R_{OFF}	47 k Ω ($t_{OFF} \cong 37 \mu\text{s}$)

Figure 3. Typical application schematic



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6 Device description

The STSPIN250 is a single brush DC motor driver integrating a PWM current controller and a power stage composed by a fully-protected full-bridge.

6.1 Standby and power-up

The device provides a low settable consumption mode forcing the STBY\RESET input below the V_{STBYL} threshold.

When the device is in the standby status, the power stage is disabled (outputs are in high impedance) and the supply to the integrated control circuitry is cut-off.

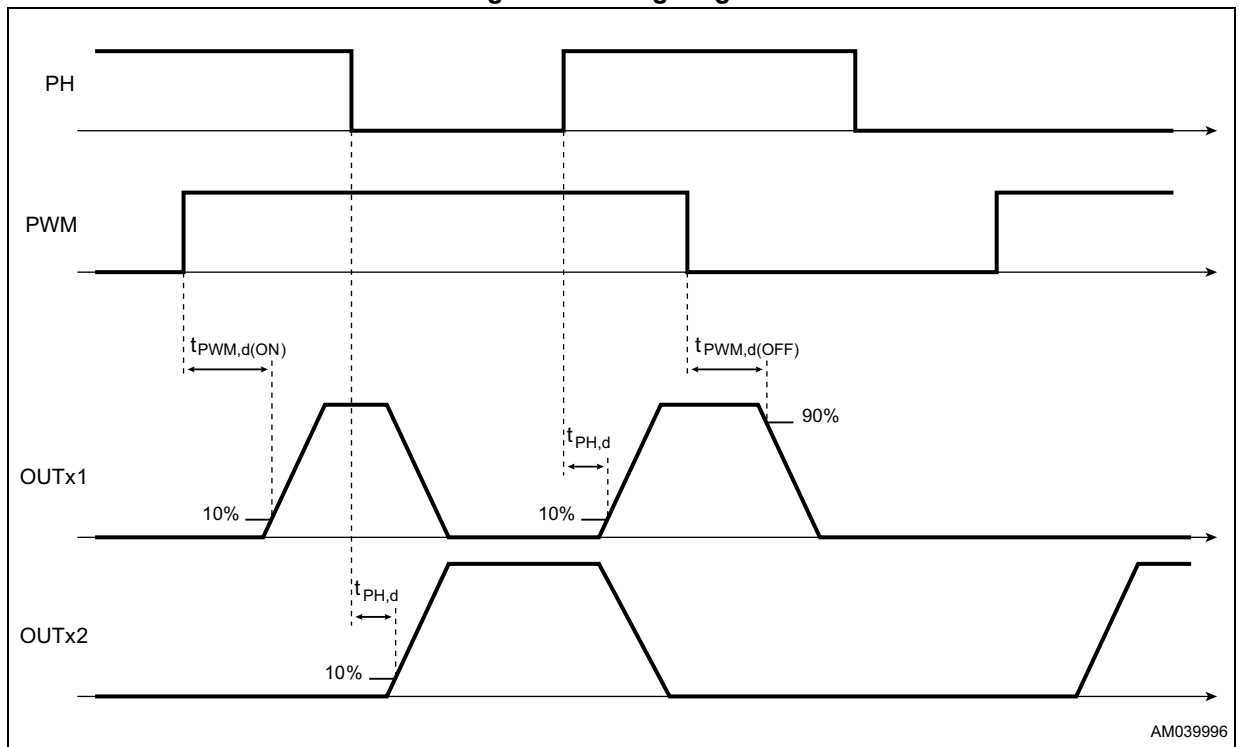
6.2 Motor driving

The outputs of the full-bridge are controlled by the PWM and PH inputs as listed in [Table 8](#).

Table 8. Truth table

ENFAULT	PH	PWM	OUTx1	OUTx2	Full-bridge condition
0	X	X	HiZ	HiZ	Disabled
1	0	0	GND	GND	Both LS on
1	0	1	GND	VS	HSx2 and LSx1 on (current X1 ← X2)
1	1	0	GND	GND	Both LS on
1	1	1	VS	GND	HSx1 and LSx2 on (current X1 → X2)

Figure 4. Timing diagram



6.3 PWM current control

The device implements a current controller.

The voltage on the sense pins (V_{SENSE}) is compared to the reference voltage applied on the REF pin (V_{REF}).

When $V_{SENSE} > V_{REF}$, the current limiter is triggered, the OFF time counter is started, and the decay sequence is performed.

The decay sequence starts turning on all the low sides of the full-bridge. After the programmed OFF time the system returns to the ON state.

Table 9. ON and slow decay states

PH	PWM	ON	Decay
0	0	HSx1 = OFF LSx1 = ON HSx2 = OFF LSx2 = ON	N.A. ⁽¹⁾
0	1	HSx1 = OFF LSx1 = ON HSx2 = ON LSx2 = OFF	HSx1 = OFF LSx1 = ON HSx2 = OFF LSx2 = ON
1	0	HSx1 = OFF LSx1 = ON HSx2 = OFF LSx2 = ON	N.A. ⁽¹⁾
1	1	HSx1 = ON LSx1 = OFF HSx2 = OFF LSx2 = ON	HSx1 = OFF LSx1 = ON HSx2 = OFF LSx2 = ON

1. During decays the input values are ignored until the system returns to ON condition (decay time expired).

The reference voltage value, V_{REF} , has to be selected according to the load current target value (peak value) and sense resistors value.

Equation 1

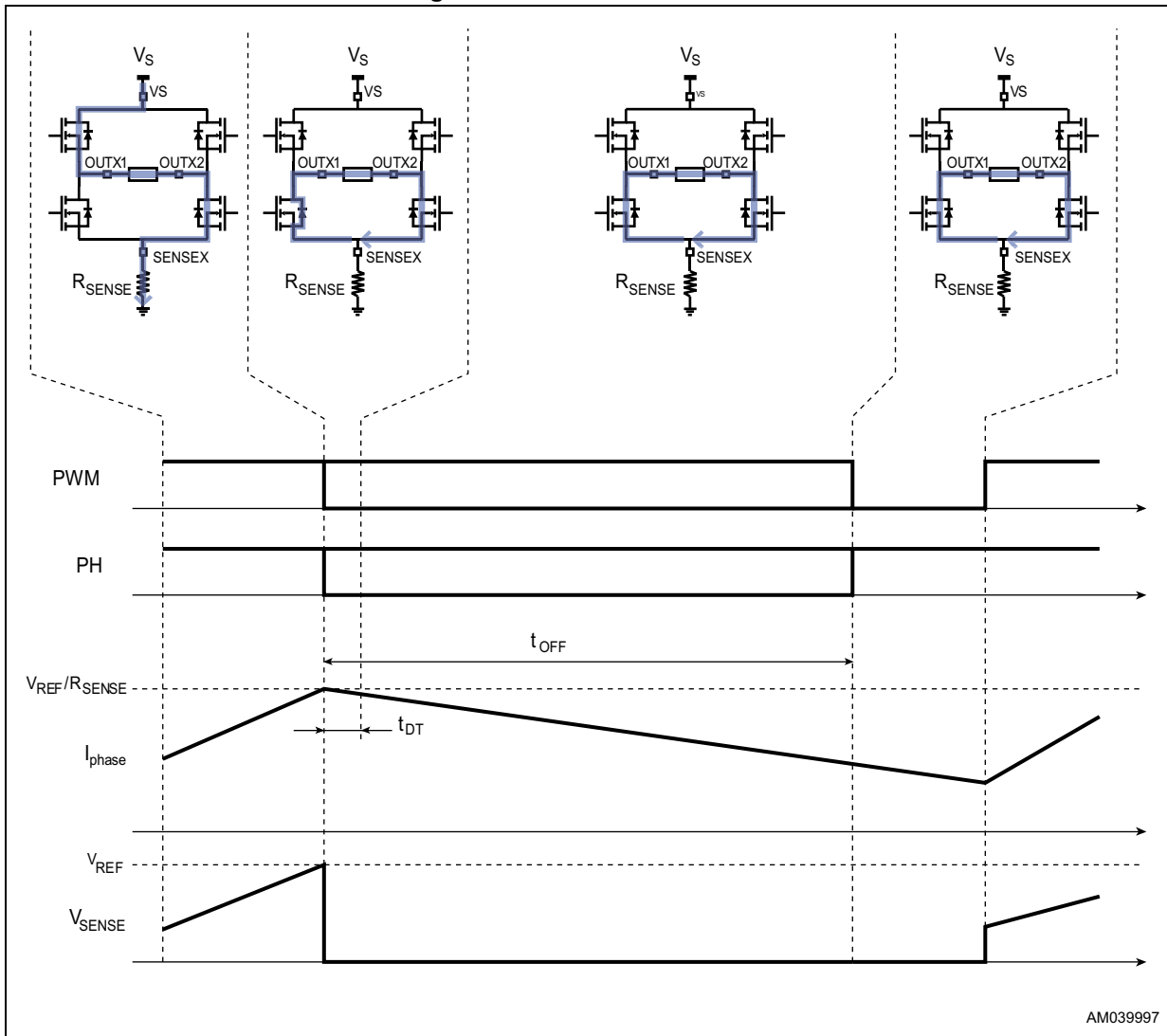
$$V_{REF} = R_{SNSx} \cdot I_{LOAD,peak}$$

In choosing the sense resistors value, two main issues must be taken into account:

- The sensing resistor dissipates energy and provides dangerous negative voltages on the SENSE pins during the current recirculation. For this reason the resistance of this component should be kept low (using multiple resistors in parallel will help obtaining the required power rating with standard resistors).
- The lower is the R_{SNSx} value, the higher is the peak current error due to noise on the V_{REF} pin and to the input offset of the current sense comparator: too low values of R_{SNSx} must be avoided.



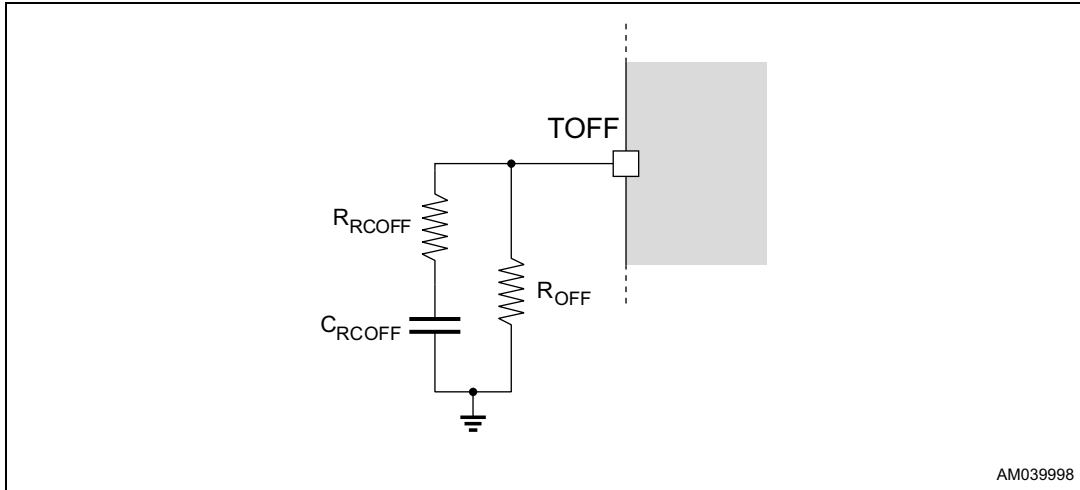
Figure 5. PWM current control



TOFF adjustment

The decay time is adjusted through an external resistor connected between the TOFF pin and ground as shown in [Figure 6](#). A small RC series must be inserted in parallel with the regulator resistor in order to increase the stability of the regulation circuit according indications listed in [Table 10](#).

Figure 6. OFF time regulation circuit

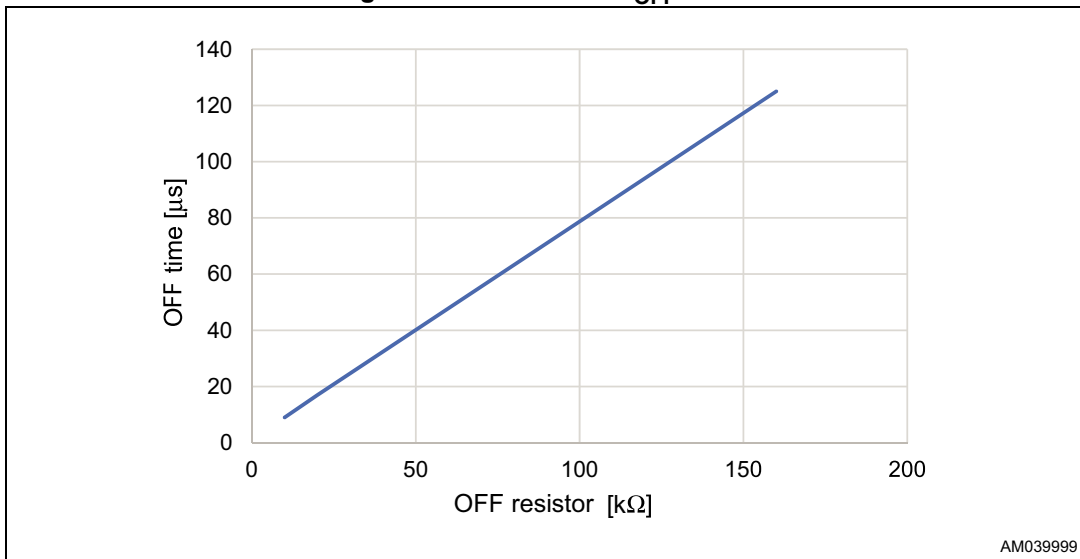


The relation between the OFF time and the external resistor value is shown in the graph of [Figure 7](#). The value typically ranges from 10 μ s to 150 μ s.

Table 10. Recommended R_{RCOFF} and C_{RCOFF} values according to R_{OFF}

R_{OFF}	R_{RCOFF}	C_{RCOFF}
$10\text{ k}\Omega \leq R_{OFF} < 82\text{ k}\Omega$	1 k Ω	22 nF
$82\text{ k}\Omega \leq R_{OFF} \leq 160\text{ k}\Omega$	2.2 k Ω	22 nF

Figure 7. OFF time vs R_{OFF} value



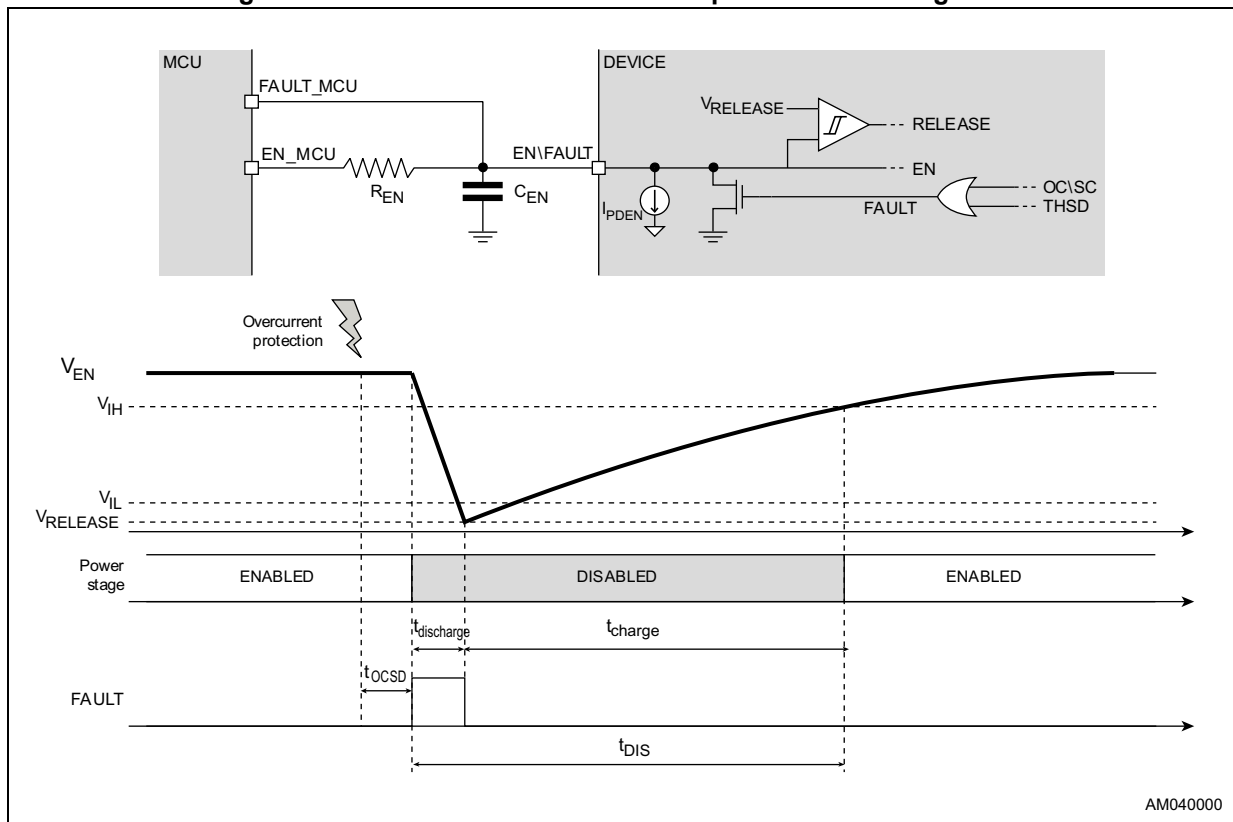
6.4 Overcurrent and short-circuit protections

The device embeds circuitry protecting each power output against the overload and short-circuit conditions (short-circuit to ground, short-circuit to VS and short-circuit between outputs).

When the overcurrent or the short-circuit protection is triggered, the power stage is disabled and the EN\FAULT input is forced low through the integrated open-drain MOSFET discharging the external C_{EN} capacitor.

The power stage is kept disabled and the open-drain MOSFET is kept ON until the EN\FAULT input falls below the V_{RELEASE} threshold, then the C_{EN} capacitor is charged through the R_{EN} resistor.

Figure 8. Overcurrent and short-circuit protections management



The total disable time after an overcurrent event can be set by properly sizing the external network connected to the EN\FAULT pin (refer to [Figure 9](#) and [Figure 10](#)):

Equation 2

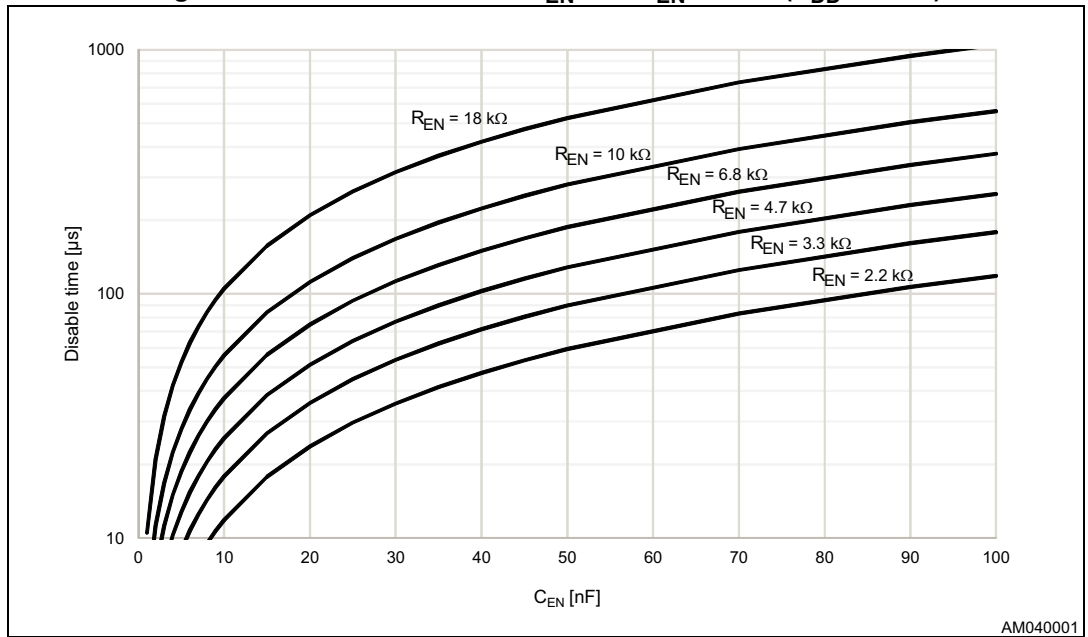
$$t_{DIS} = t_{discharge} + t_{charge}$$

But t_{charge} is normally very higher than t_{discharge} we can consider only the second one contribution:

$$t_{DIS} \cong R_{EN} \cdot C_{EN} \cdot \ln \frac{(V_{DD} - R_{EN} \cdot I_{PD}) - V_{RELEASE}}{(V_{DD} - R_{EN} \cdot I_{PD}) - V_{IH}}$$

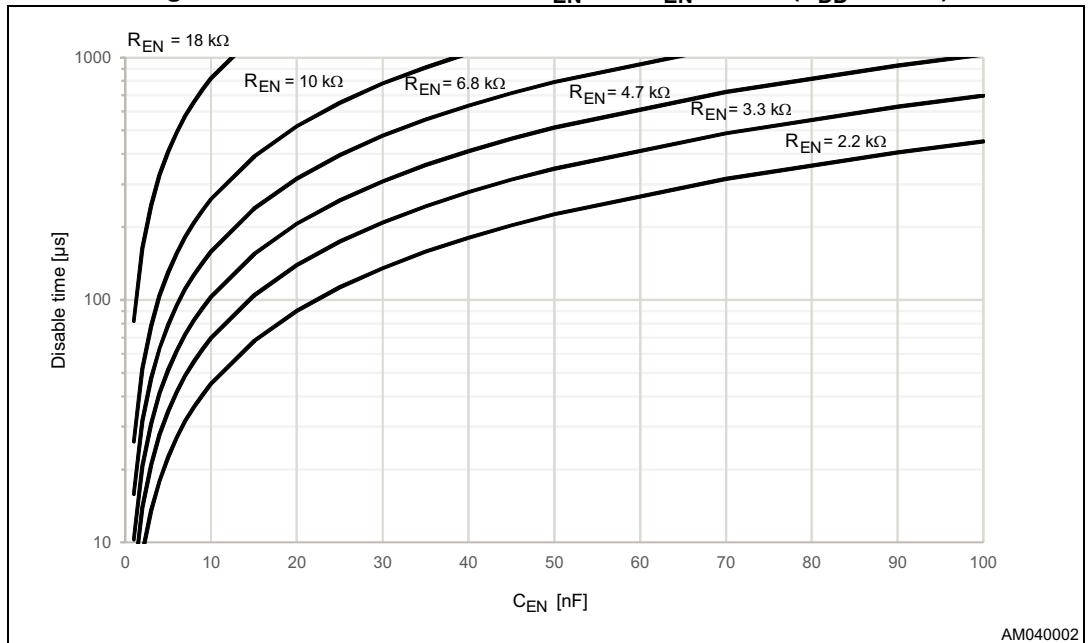
Where V_{DD} is the pull-up voltage of the R_{EN} resistor.

Figure 9. Disable time versus R_{EN} and C_{EN} values ($V_{DD} = 3.3\text{ V}$)



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Figure 10. Disable time versus R_{EN} and C_{EN} values ($V_{DD} = 1.8\text{ V}$)



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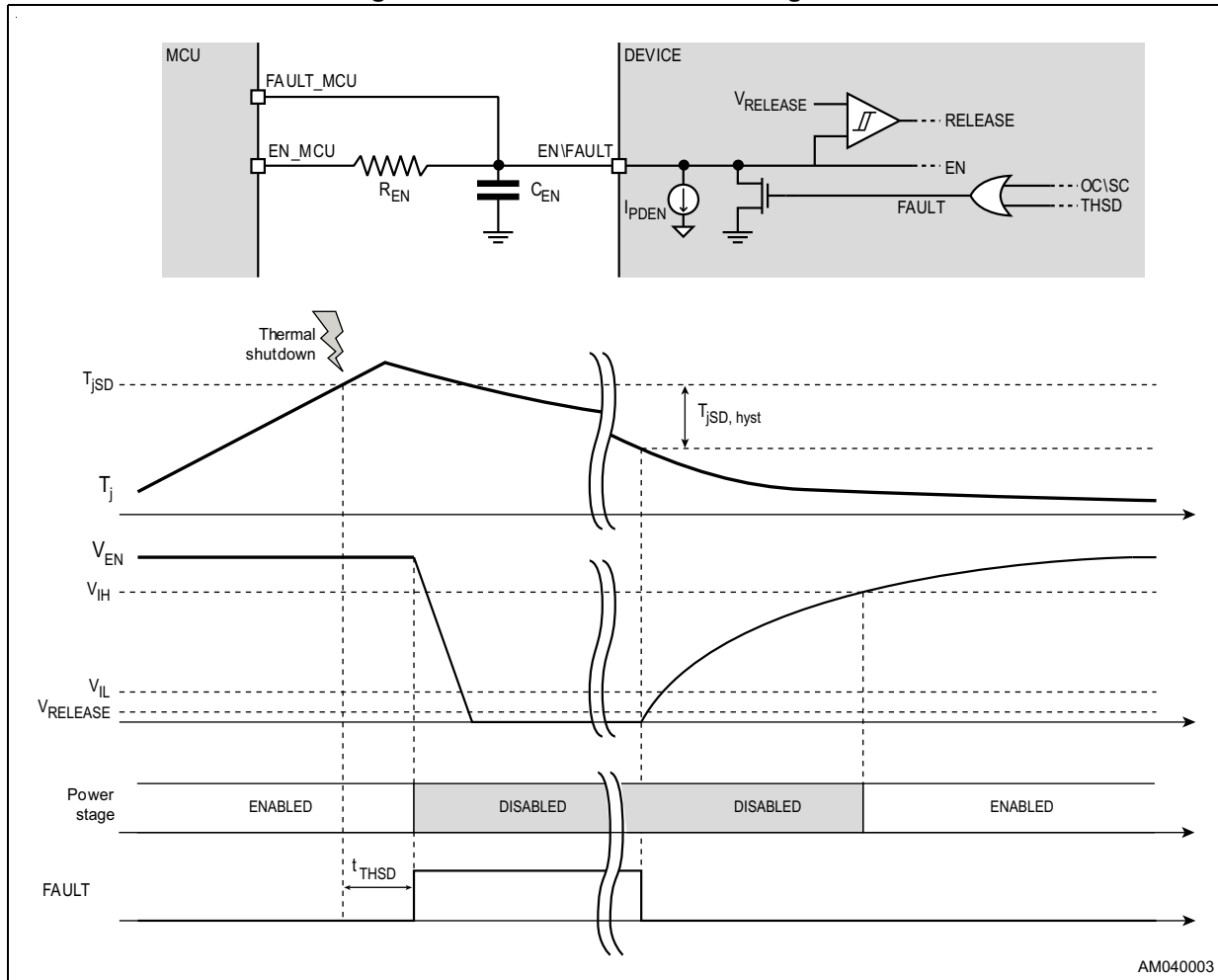
6.5 Thermal shutdown

The device embeds circuitry protecting it from the overtemperature condition.

When the thermal shutdown temperature is reached the power stage is disabled and the EN\FAULT input is forced low through the integrated open-drain MOSFET.

The protection and the EN\FAULT output are released when the IC temperature returns below a safe operating value ($T_{jSD} - T_{jSD,Hyst}$).

Figure 11. Thermal shutdown management



AM040003

7 Graphs

Figure 12. Power stage resistance versus supply voltage

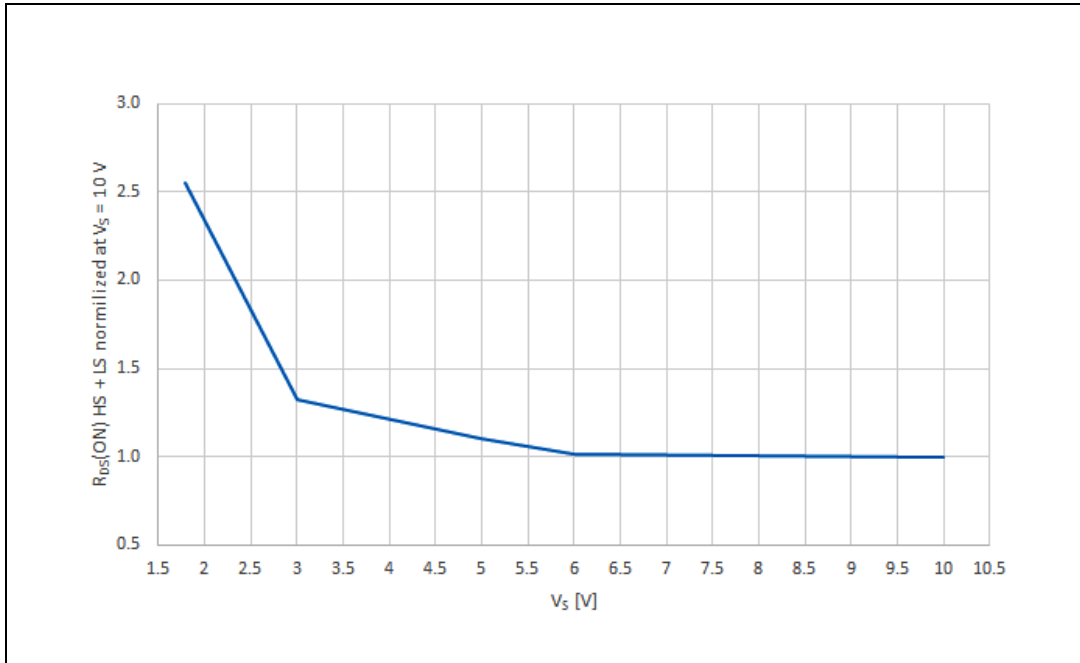
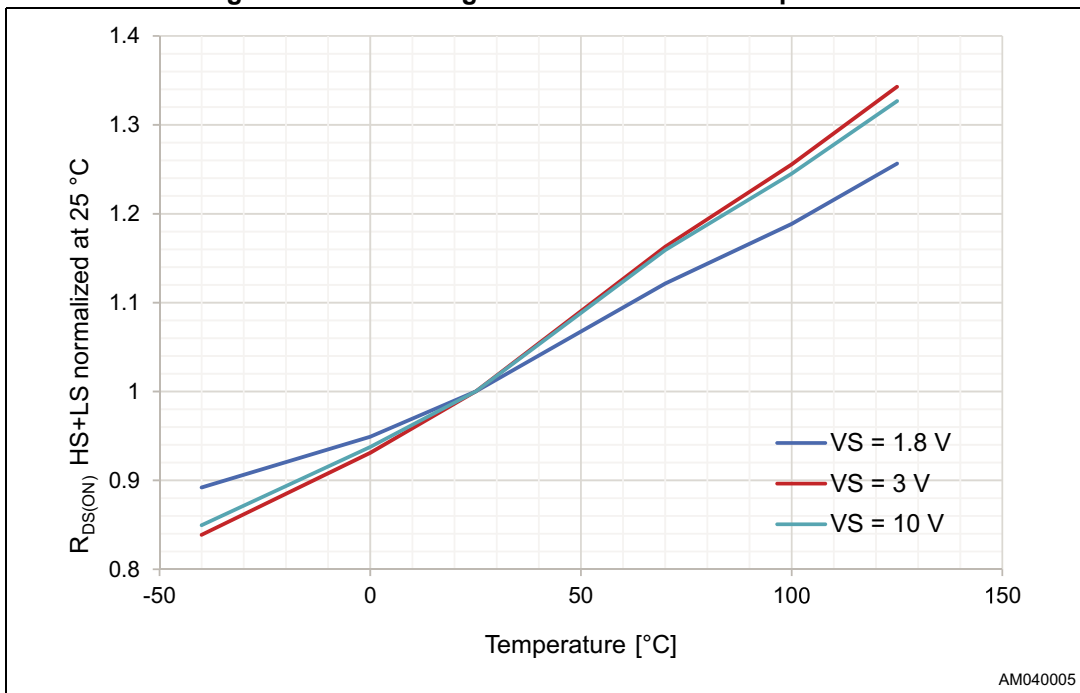
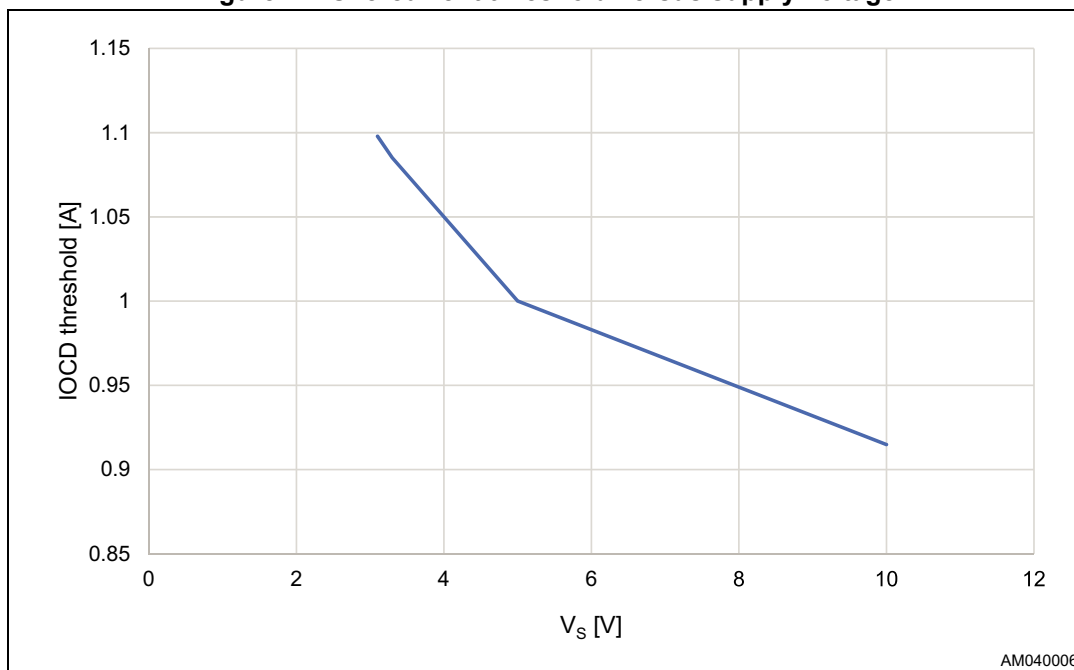


Figure 13. Power stage resistance versus temperature



AM040005

Figure 14. Overcurrent threshold versus supply voltage



8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

8.1 VFQFPN 3 x 3 x 1.0- 16L package information

Figure 15. VFQFPN 3 x 3 x 1.0 - 16L package outline

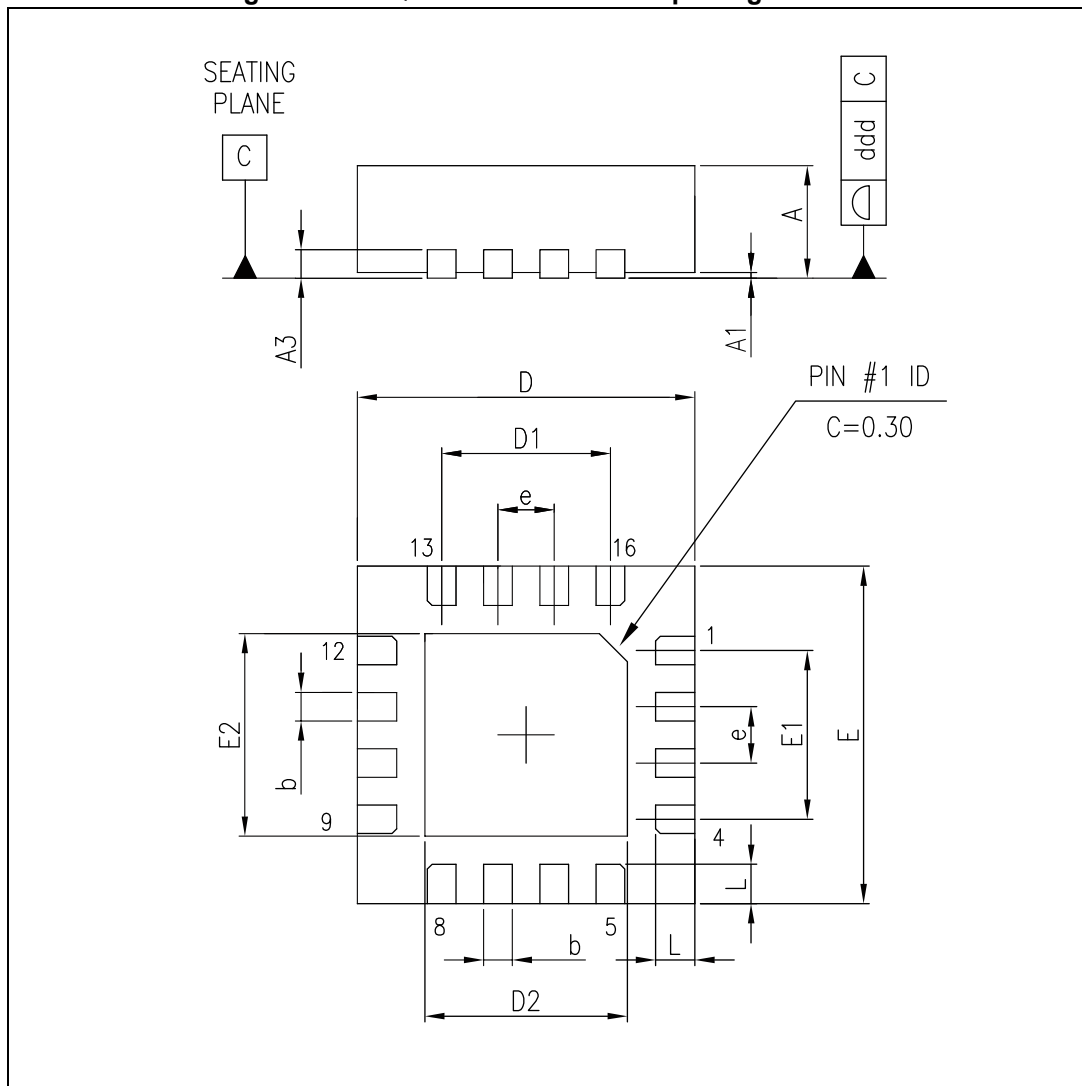
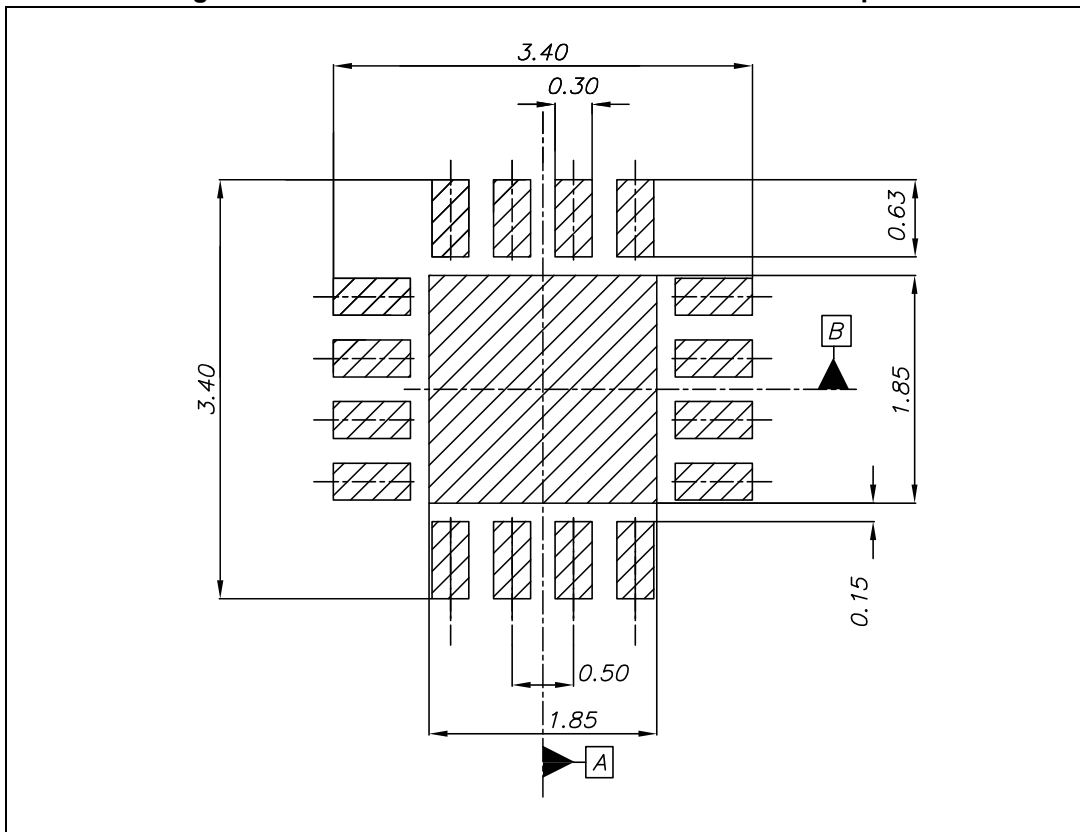


Table 11. VFQFPN 3 x 3 x 1.0 - 16L package mechanical data⁽¹⁾

Symbol	Dimensions (mm)		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	-	0.02	-
A3	-	0.20	-
b	0.18	0.25	0.30
D	2.85	3.00	3.15
D2	1.70	1.80	1.90
E	2.85	3.00	3.15
E2	1.70	1.80	1.90
e	-	0.50	-
L	0.45	0.50	0.55

- VFQFPN stands for "Thermally Enhanced Very thin Fine pitch Quad Packages No lead".
 Very thin: $0.80 < A \leq 1.00$ mm / fine pitch: $e < 1.00$ mm.
 The pin #1 identifier must exist on the top surface of the package by using indentation mark or other feature of the package body.

Figure 16. VFQFPN 3 x 3 x 1.0 - 16L recommended footprint



9 Ordering information

Table 12. Device summary

Order code	Package	Packaging
STSPIN250	VFQFPN 3 x 3 x1.0 - 16L	Tape and reel

10 Revision history

Table 13. Document revision history

Date	Revision	Changes
17-Oct-2016	1	Initial release.
04-Nov-2016	2	Updated document status to: <i>Datasheet - production data</i> on page 1. Updated Figure 1 on page 5 and Figure 12 on page 21 (replaced by new figures). Updated Table 2 on page 6 (added new parameter t_{INW}). Minor modifications throughout document.

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